

N-channel TrenchMOS logic level FET

13 July 2012

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### **1.2 Features and benefits**

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with Vgst(th) rating of greater than 0.5V at 175 °C

### 1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	234	W
Static charac	teristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	2.6	3.1	mΩ
Dynamic cha	racteristics				1		
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; Fig. 13; Fig. 14		-	25.8	-	nC

[1] Continuous current is limited by package.

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# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF44
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

# 3. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
BUK963R1-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> = 25 °C		-10	10	V
		$T_j = 25 \text{ °C};$ lifetime = 100 hours		-15	15	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>	[1]	-	100	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	794	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	234	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	794	А

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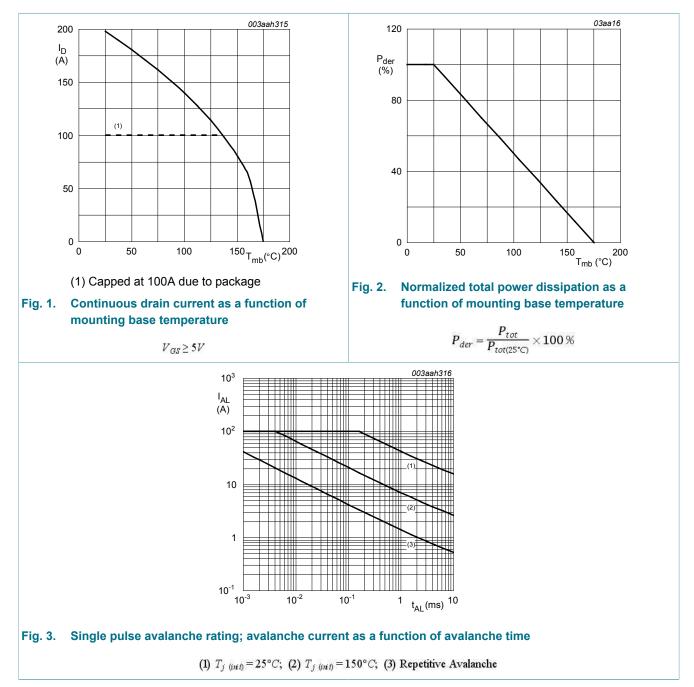
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Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rug	gedness					-
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 100 \text{ A}; \text{ V}_{sup} \leq 40 \text{ V}; \text{ R}_{GS} = 50 \Omega; \\ \text{V}_{GS} &= 5 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$	[ <u>2][3]</u>	-	419	mJ

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

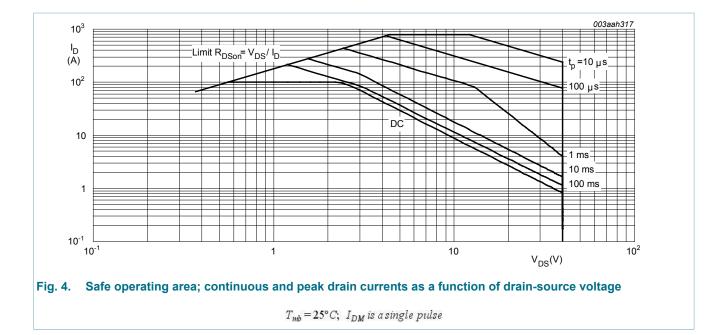


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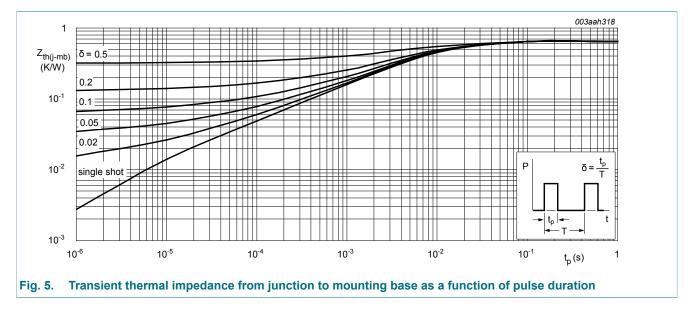
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### 5. Thermal characteristics

Table 5. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.64	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W



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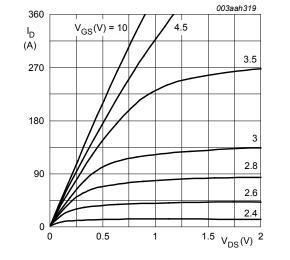
# 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·	I			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = -55 \text{ °C;}$ Fig. 9	-	-	2.45	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 9	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.06	1	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	2.6	3.1	mΩ
resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	2.25	2.7	mΩ	
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	6	mΩ
Dynamic cl	naracteristics	· · · · ·	I	I	1	
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 5 V;	-	69.5	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	16.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	25.8	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;	-	6870	9150	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	875	1050	pF
C <sub>rss</sub>	reverse transfer capacitance		-	450	620	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V;	-	42	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	73	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	114	-	ns
t <sub>f</sub>	fall time		-	76	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH

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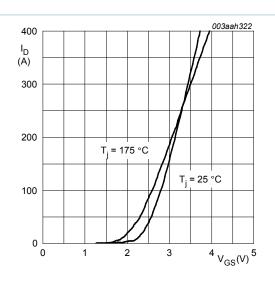
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Source-drain	diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V_{\rm GS} = 0 V;	-	40	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	47	-	nC



T<sub>j</sub> = 25 °C; t<sub>p</sub> = 300 μs







 $V_{DS} = 10V$ 

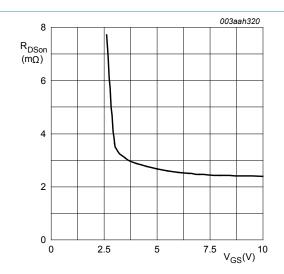
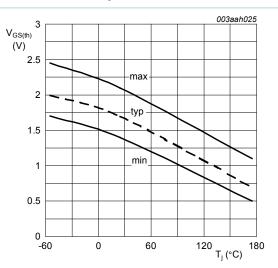


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$ 

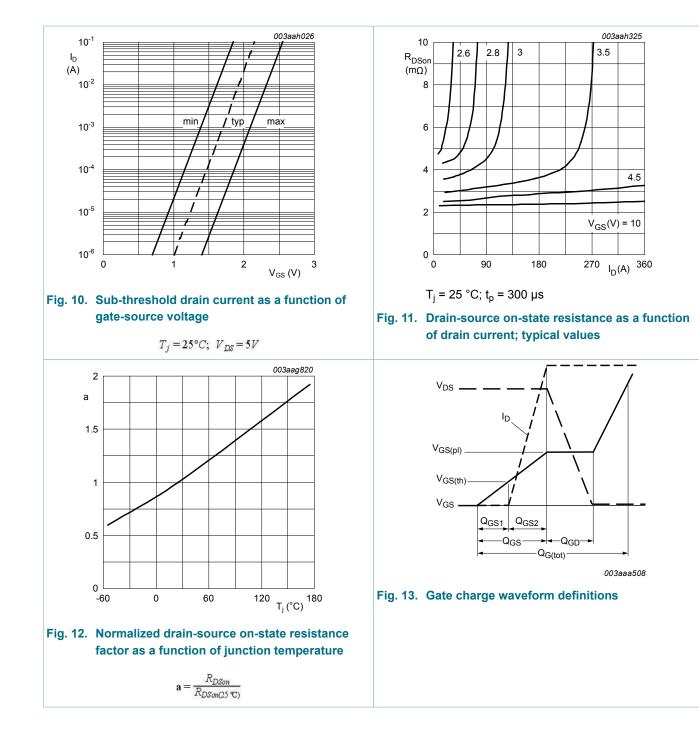




 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$ 

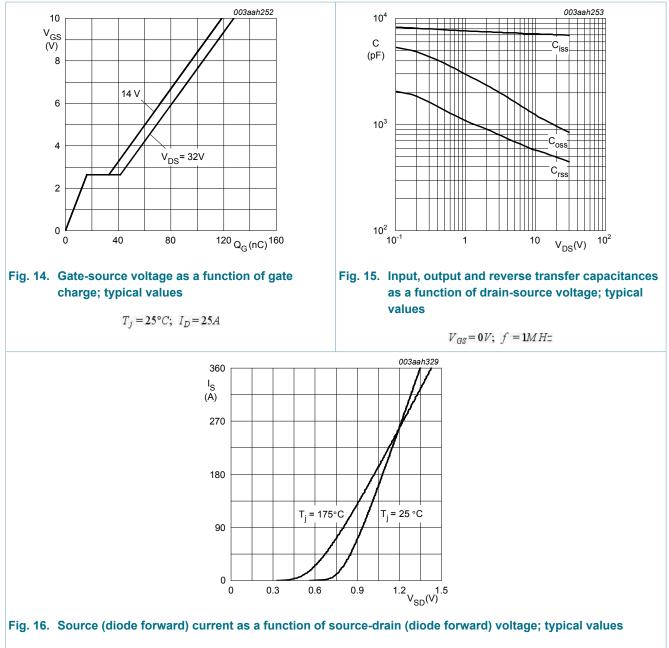
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 $V_{GS} = \mathbf{0} V$ 

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#### **Package outline** 7.

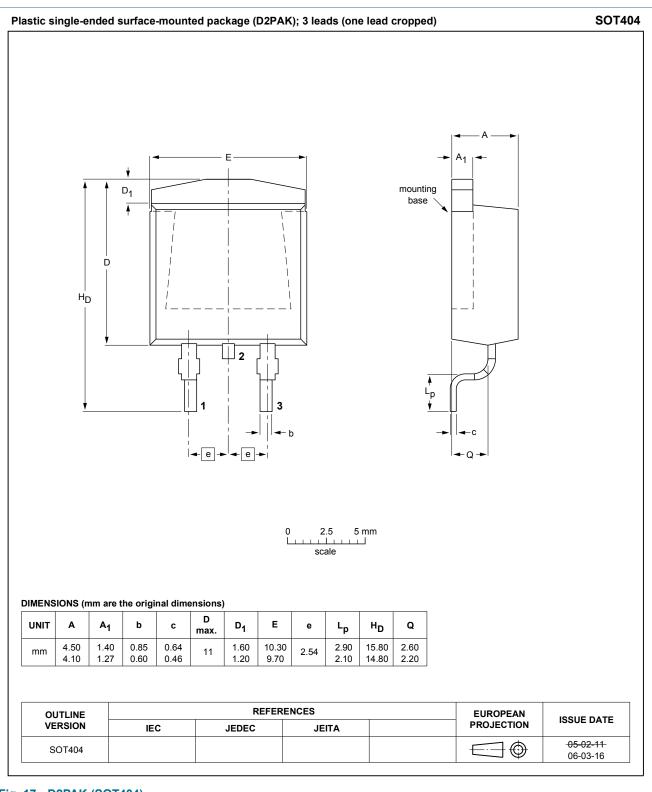


Fig. 17. D2PAK (SOT404)

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### 8. Legal information

#### 8.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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